3-Vrms Cap-Less Line Driver with Adjustable Gain

Features

- Operation Voltage: 3V to 5.5V
- Cap-less Output
  - Eliminates Output Capacitors
  - Improves Low Frequency Response
  - Reduces POP/Clicks
- Low Noise and THD
  - SNR > 102dB
  - Typical Vn < 12uVrms
  - THD+N < 0.02%
- Maximum Output Voltage Swing into 2.5k Load
  - 2Vrms at 3.3V Supply Voltage
  - 3Vrms at 5V Supply Voltage
- Differential Input
- External Gain Setting from 1V/V to 10V/V
- Fast Start-up Time : 0.5ms
- Integrated De-Pop Control
- External Under Voltage Protection
- Thermal Protection
- Less External Components Required
- +/-8kV IEC ESD Protection at line outputs

Applications

- LCD / PDP TVs
- CD / DVD players
- Set-Top Boxes
- Home Theater in Box

Description

The AD22650 is a 3-Vrms cap-less stereo line driver. The device is ideal for single supply electronics. Cap-less design can eliminate output dc-blocking capacitors for better low frequency response and save cost.

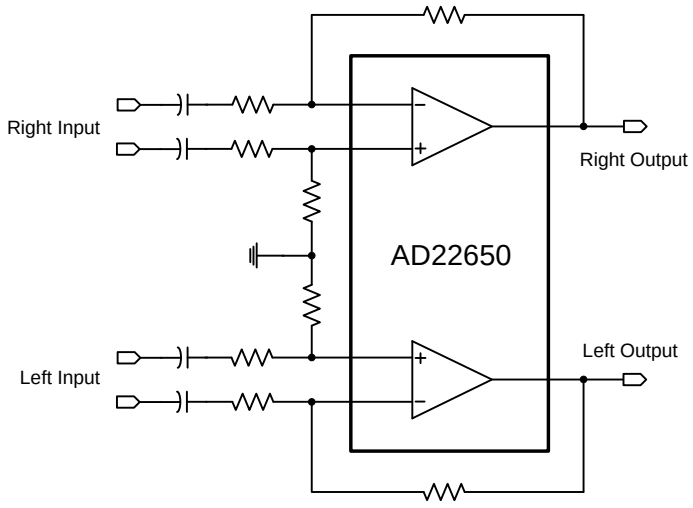
The AD22650 is capable of delivering 3-Vrms output into a 2.5kΩ□load with 5V supply. The gain settings can be set by users from 1V/V to 10V/V externally. The AD22650 has internal and external under voltage protection to prevent POP noise. Build-in shutdown control and de-pop control sequence also help AD22650 to be a pop-less device.

The AD22650 is available in a 14-pin TSSOP package.

Ordering Information

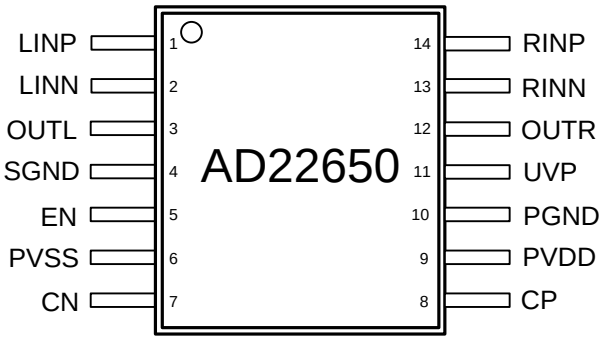
Product ID	Package	Packing	Comments
AD22650-QH14NAT	TSSOP-14	96 Units / Tube 100 Tubes / Small Box	Green(HF)
AD22650-QH14NAR		2.5k Units Tape & Reel	

Simplified Application Circuit



Pin Assignments

TSSOP-14
(Top View)

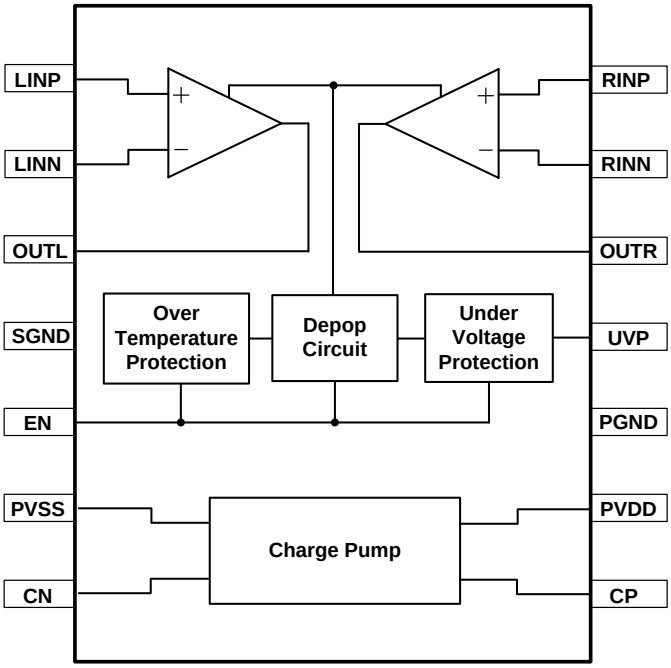


Pin Description

No.	Name	Type (1)	Pin Description
1	LINP	I	Left channel OP positive input
2	LINN	I	Left channel OP negative input
3	OUTL	O	Left channel OP output
4	SGND	P	Signal ground
5	EN	I	Enable input, active high
6	PVSS	P	Supply voltage
7	CN	I/O	Charge-pump flying capacitor negative terminal
8	CP	I/O	Charge-pump flying capacitor positive terminal
9	PVDD	P	Positive supply
10	PGND	P	Power ground
11	UVP	I	Under-voltage protection input, internally pulled high
12	OUTR	O	Right channel OP output
13	RINN	I	Right channel OP negative input
14	RINP	I	Right channel OP positive input

(1) I=input, O=output, P=power

Functional Block Diagram



Available Package

Package Type	Device No.	Θ_{ja} (℃/W)(1)	Θ_{jc} (℃/W)(2)
TSSOP-14	AD22650	100	32

(1) Θ_{ja} is measured at room temperature (TA=25℃), natural convection environment test board, which is constructed with a thermal efficient, 2-layers PCB. The measurement is tested using the JEDEC51-3 thermal measurement standard.

(2) Θ_{jc} represents the heat resistance for the heat flow between the chip and package's top surface.

Marking Information

AD22650
Line 1 : LOGO
Line 2 : Product No.
Line 3 : Tracking Code
Line 4 : Date Code



Absolute Maximum Ratings(1)

SYMBOL	PARAMETER	VALUE	UNIT
	Supply Voltage, V_{DD} to GND	-0.3 to 6.0	V
V_I	Input Voltage	VSS -0.3 to VDD+0.3	V
R_L	Minimum load impedance	16	Ω
	EN to GND	-0.3 to VDD+0.3	V
T_{stg}	Storage temperature range	-65 to 150	℃
T_J	Maximum operating junction temperature range	-40 to 150	℃

(1) The absolute maximum ratings are limiting values of operation, safety of the device cannot be guaranteed if beyond those values.

Recommended Operating Conditions

SYMBOL	PARAMETER		Min	NOM	Max	UNIT
V_{DD}	Supply Voltage		3.0		5.5	V
V_{IH}	High Level Input Voltage	EN	60			% of V_{DD}
V_{IL}	Low Level Input Voltage	EN			40	% of V_{DD}
T_A	Operating Ambient Temperature Range		-40		85	℃
R_L	Load Resistance		16			Ω

Electrical Characteristics

PVDD=3.3V, T_A=25℃, R_L=2.5kΩ, C_{FLY}=C_{PVSS}=1μF, C_{IN}=1μF, R_I=10kΩ, R_F=20kΩ (unless otherwise noted)

SYMBOL	PARAMETER	TEST CONDITIONS	Min	NOM	Max	UNIT
I_{DD}	V_{DD} Supply Current	EN=V_{DD}		7	15	mA
I_{SD}	V_{DD} Shutdown Current	EN=0V, V_{DD} =5.5V			5	μA
II	Input Current	EN pin		0.1		μA
V_O	Output Voltage (Outputs In Phase)	THD+N=1%, V_{DD}=3.3V, f_{IN}=1kHz		2.2		Vrms
		THD+N=1%, V_{DD}=5V, f_{IN}=1kHz		3.4		
		THD+N=1%, V_{DD}=5V, f_{IN}=1kHz, RL=100k		3.5		
Po	Output Power (Outputs In Phase)	THD+N=1%, V_{DD}=3.3V, f_{IN}=1kHz, R_L=32Ω		19		mW
		THD+N=1%, V_{DD}=5V, f_{IN}=1kHz, R_L=32Ω		53		
		THD+N=1%, V_{DD}=3.3V, f_{IN}=1kHz, R_L=16Ω		13		
		THD+N=1%, V_{DD}=5V, f_{IN}=1kHz, R_L=16Ω		38		
THD+N	Total Harmonic Distortion Plus Noise	V_O=2Vrms, f_{IN}=1kHz		0.002		%
		Po=10mW, f_{IN}=1kHz, R_L=32Ω		0.04		

Electrical Characteristics (Con't)

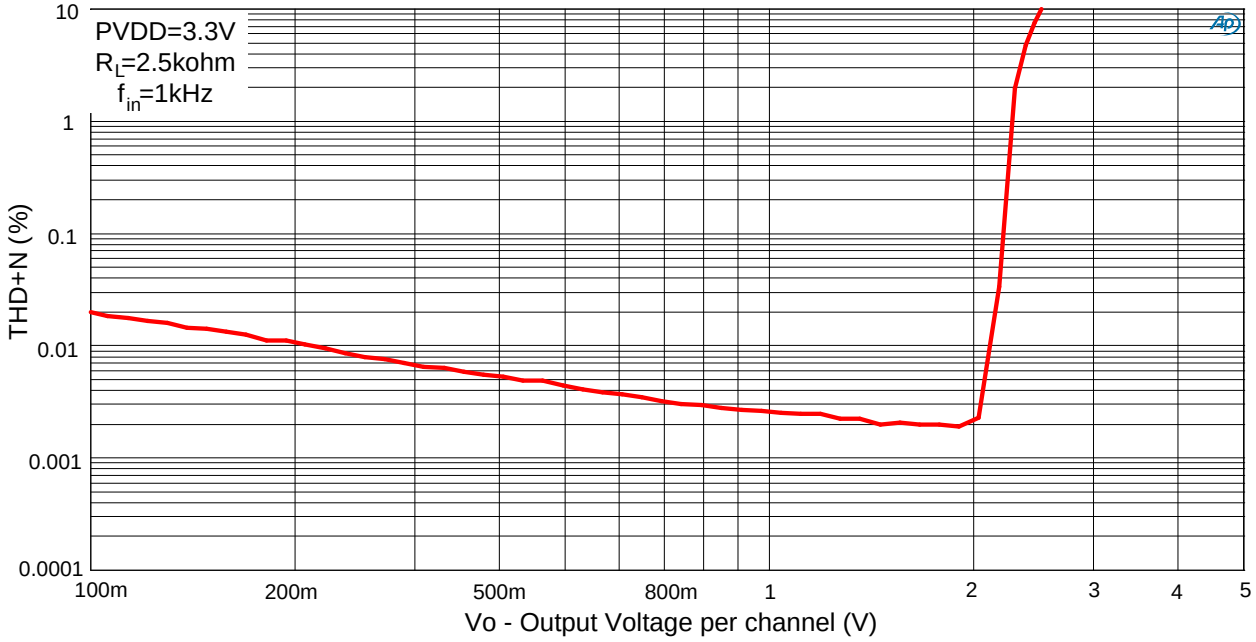
PVDD=3.3V, T_A=25℃, R_L=2.5kΩ, C_{FLY}=C_{PVSS}=1μF, C_{IN}=1μF, R_I=10kΩ, R_F=20kΩ (unless otherwise noted)

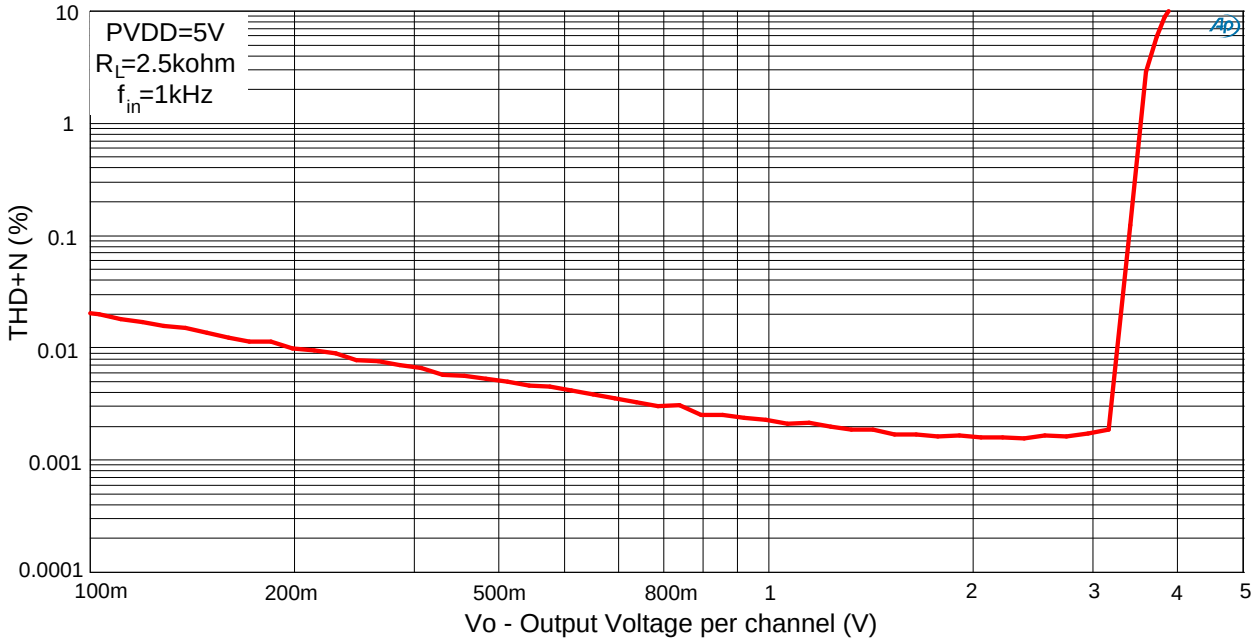
SYMBOL	PARAMETER	TEST CONDITIONS	Min	NOM	Max	UNIT
THD+N	Total Harmonic Distortion Plus Noise	Po=10mW, f_{IN}=1kHz, R_L=16Ω		0.06		%
Crosstalk	Channel Separation	V_O=2Vrms, f_{IN}=1kHz		-110		dB
		Po=10mW, f_{IN}=1kHz, R_L=32Ω		-74		
V_N	Output Noise	R_I=10k, R_F=10k		11	15	μVrms
V_{OS}	Output Offset Voltage	V_{DD}=3V to 5.5V, Input Grounded	-5		5	mV
PSRR	Power Supply Rejection Ratio	V_{DD}=3V to 5.5V, V_{rr}=200mVrms, f_{IN}=1kHz		-80	-60	dB
R_I	Input Resistor Range		1	10	47	kΩ
R_F	Feedback Resistor Range		4.7	20	100	kΩ
f_{CP}	Charge-Pump Frequency		400	500	600	kHz
	Maximum capacitive Load			220		pF
V_{UVP}	External Under Voltage Detection			1.25		V
I_{HYS}	External Under Voltage Detection Hysteresis Current			5		μA
TSD	Over Temperature Protection Level			150		℃
$T_{start-up}$	Start-up Time			0.5		ms

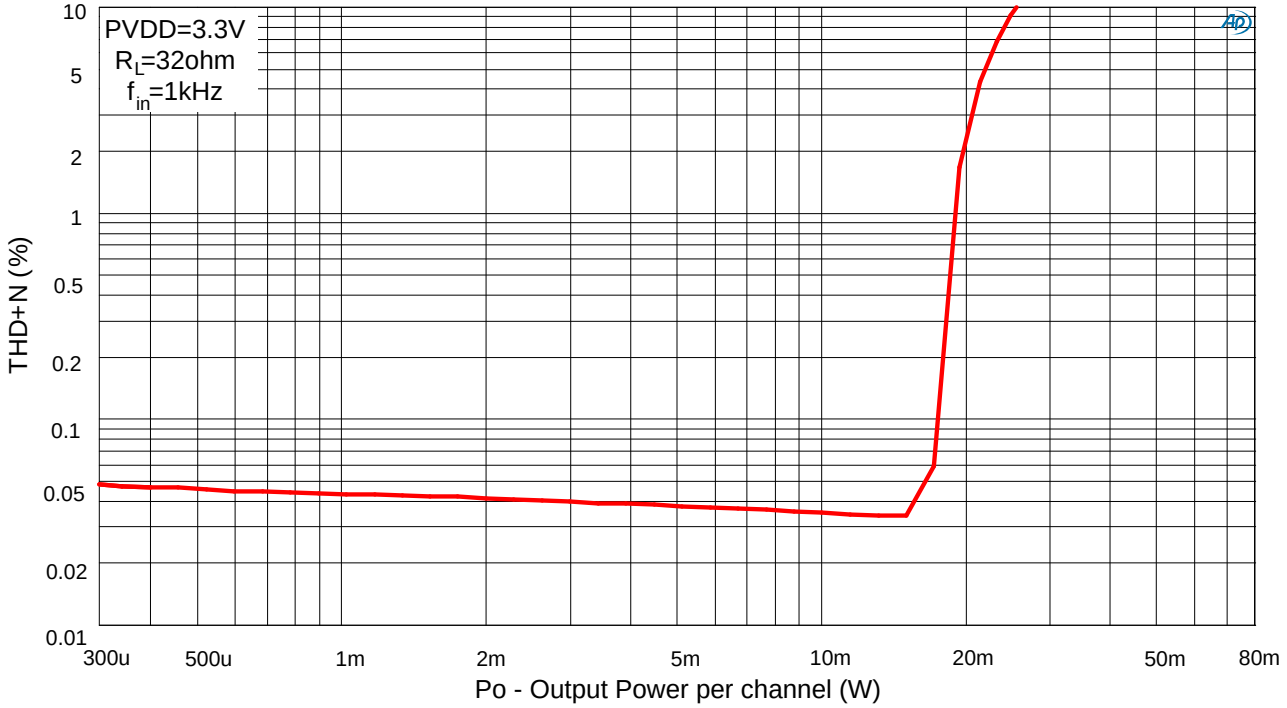
Typical Characteristics

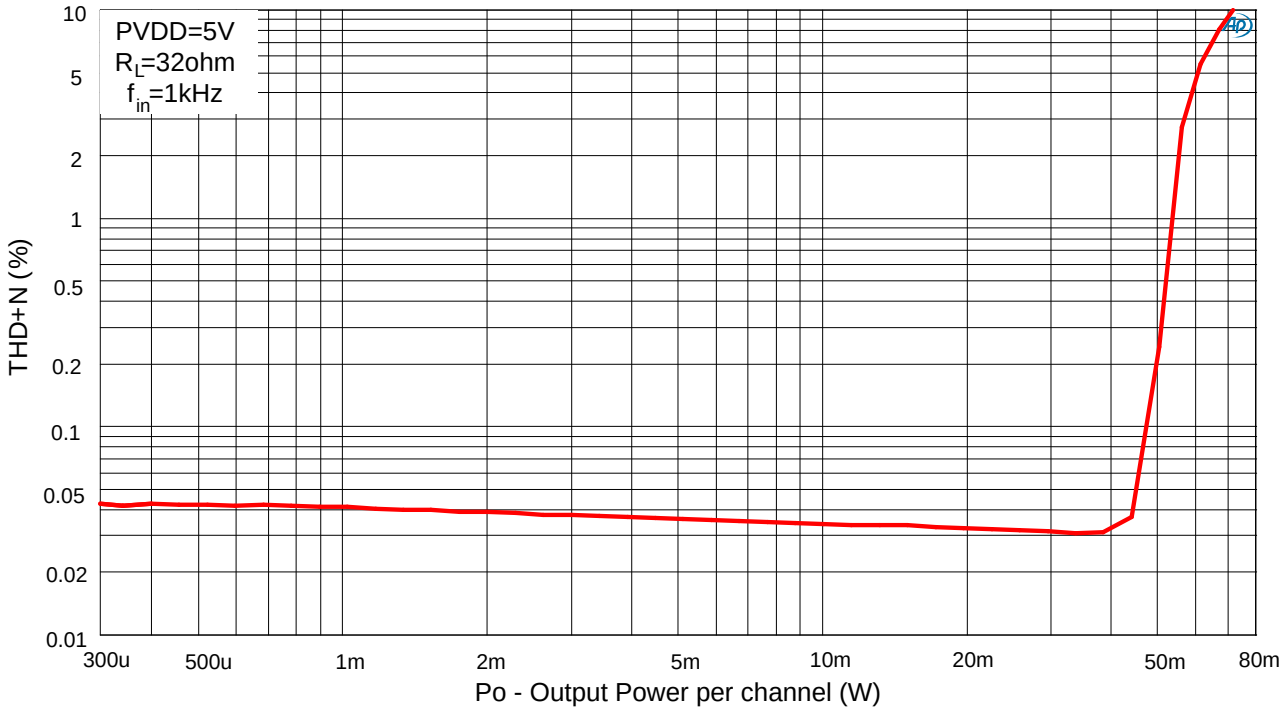
PVDD=3.3V, T_A=25℃, R_L=2.5kΩ, C_{FLY}=C_{PVSS}=1μF, C_{IN}=1μF, R_I=10kΩ, R_F=20kΩ (unless otherwise noted)

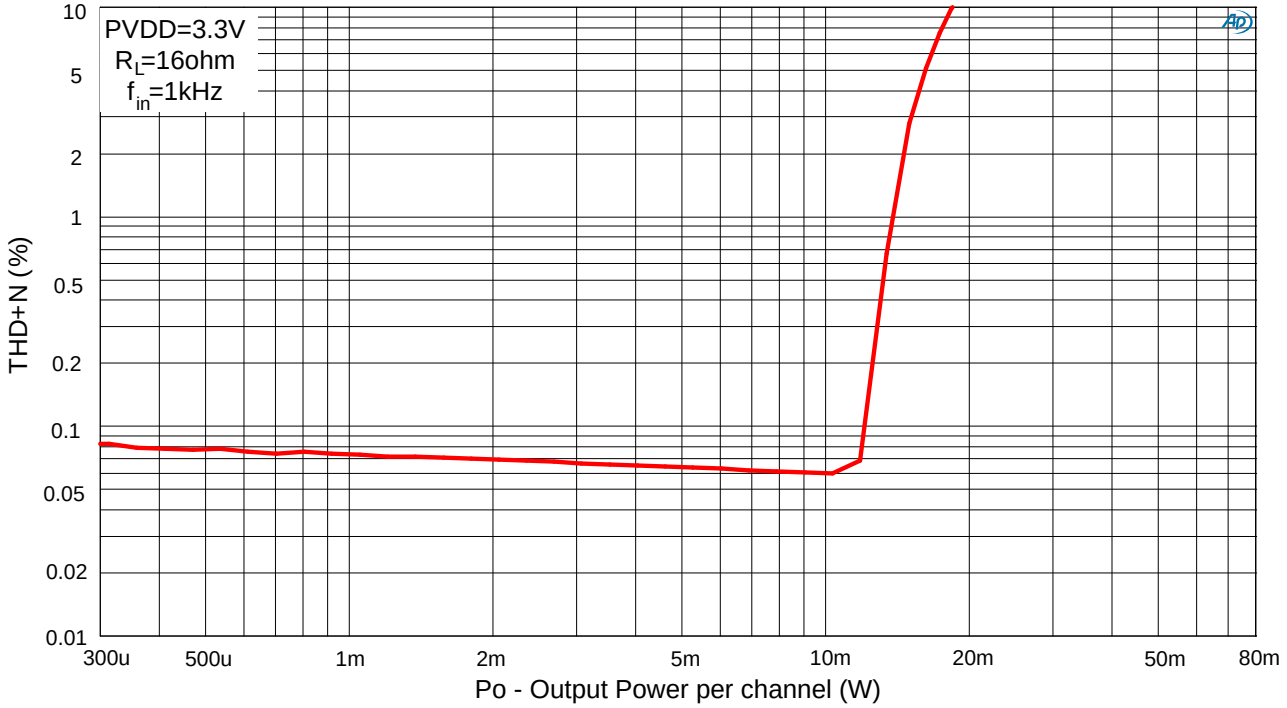
- Total Harmonic Distortion + Noise (THD+N) vs. Output Power

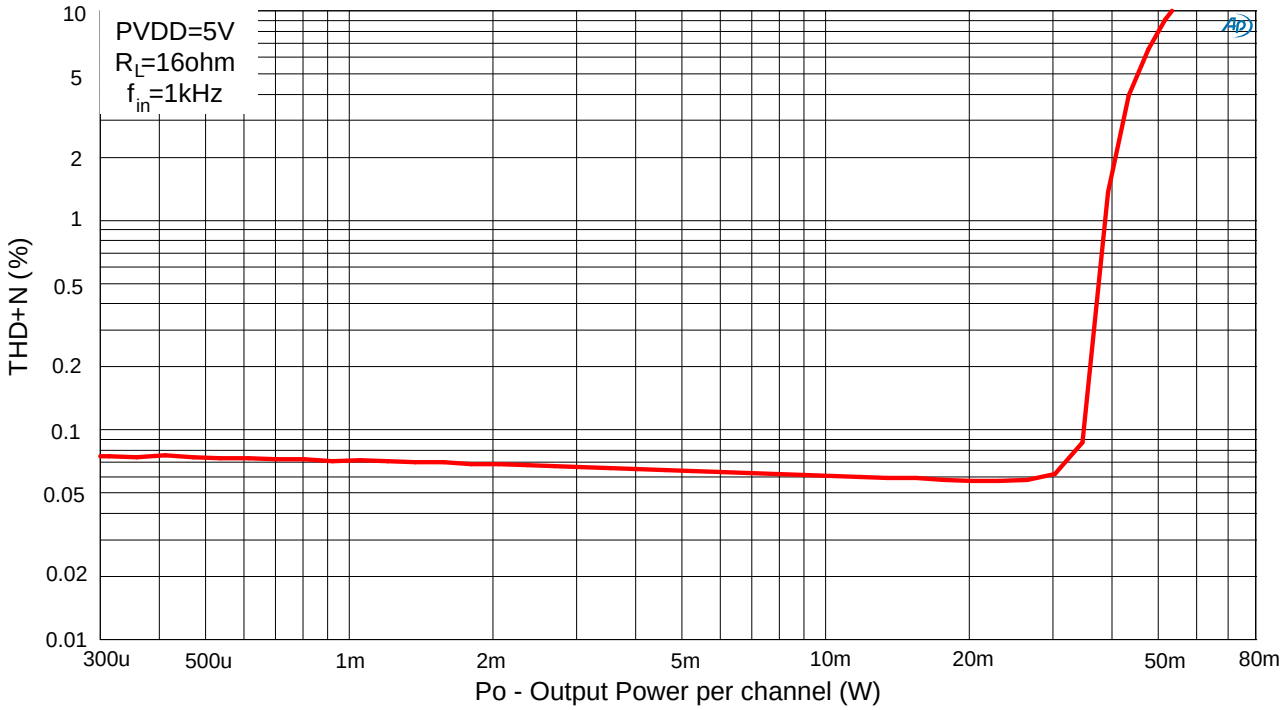




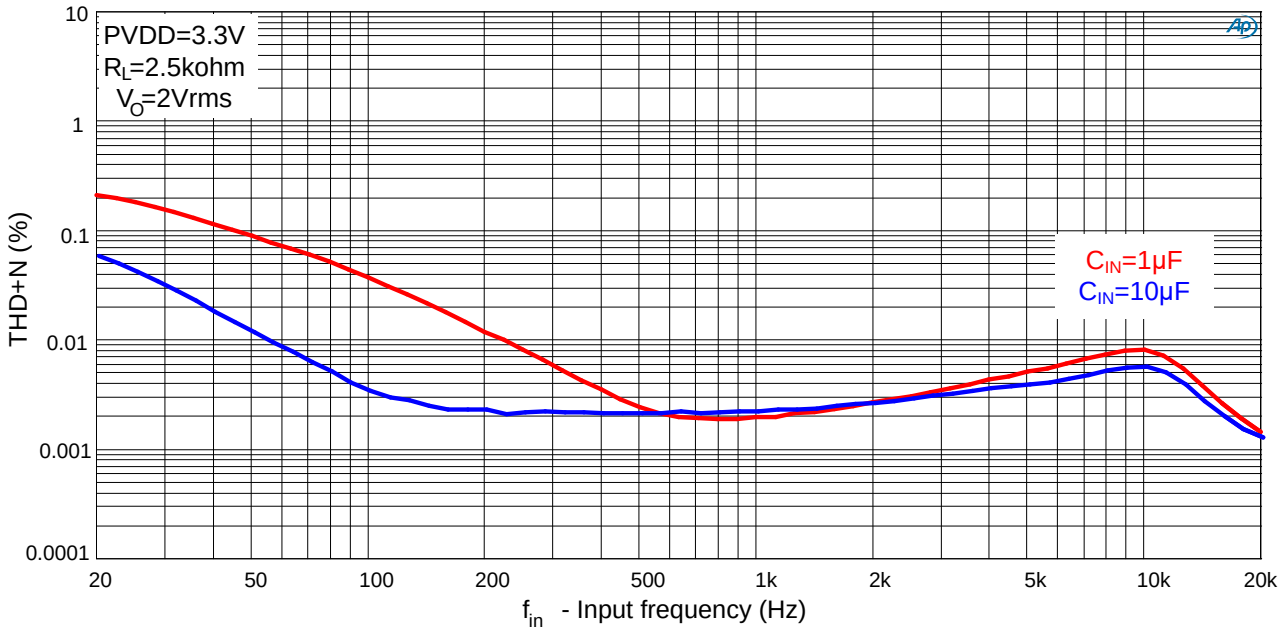

PVDD=3.3V
RL=32ohm
fin=1kHz
THD+N (%)
10
5
2
1
0.5
0.2
0.1
0.05
0.02
0.01
300u
500u
1m
2m
5m
10m
20m
50m
80m
Po - Output Power per channel (W)

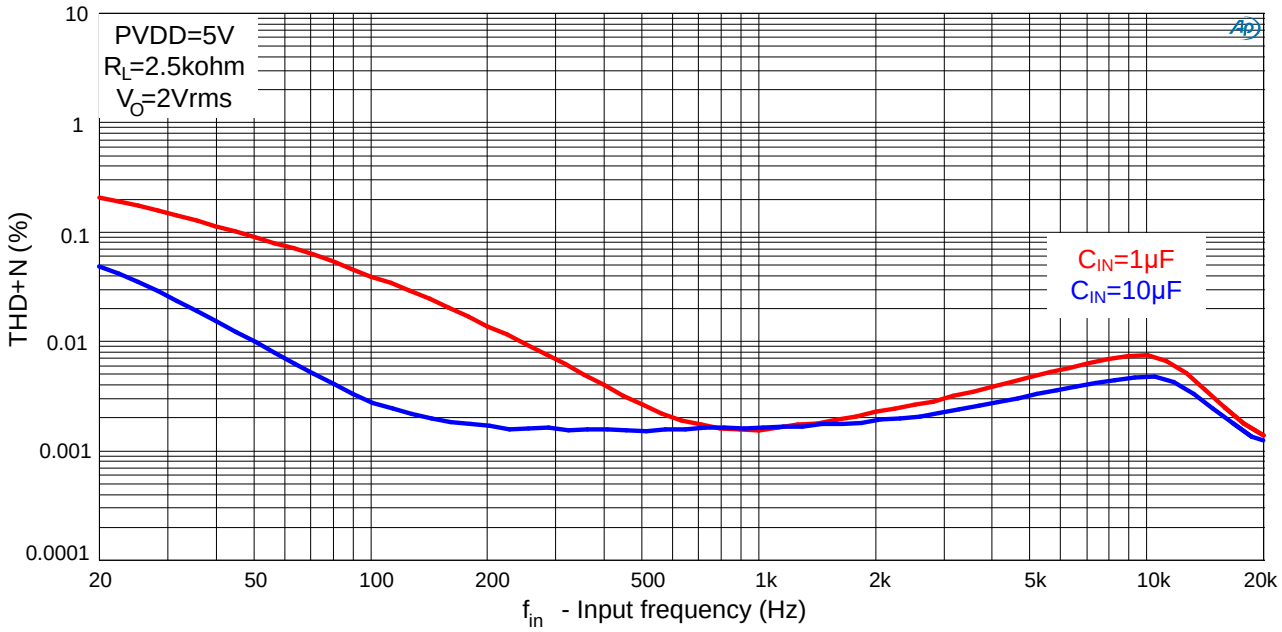

PVDD=5V
RL=32ohm
fin=1kHz
THD+N (%)
10
5
2
1
0.5
0.2
0.1
0.05
0.02
0.01
300u
500u
1m
2m
5m
10m
20m
50m
80m
Po - Output Power per channel (W)


PVDD=3.3V
RL=16ohm
fin=1kHz
THD+N (%)
10
5
2
1
0.5
0.2
0.1
0.05
0.02
0.01
300u
500u
1m
2m
5m
10m
20m
50m
80m
Po - Output Power per channel (W)

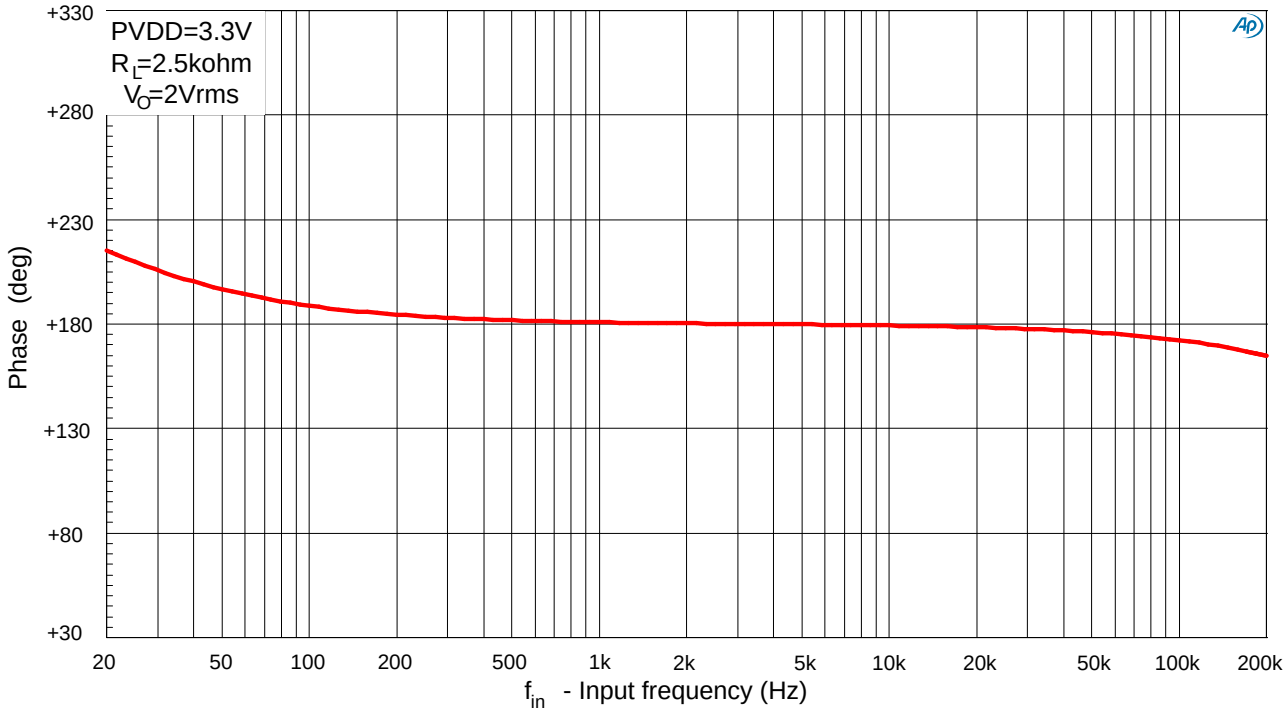

PVDD=5V
RL=16ohm
fin=1kHz
THD+N (%)
10
5
2
1
0.5
0.2
0.1
0.05
0.02
0.01
300u
500u
1m
2m
5m
10m
20m
50m
80m
Po - Output Power per channel (W)

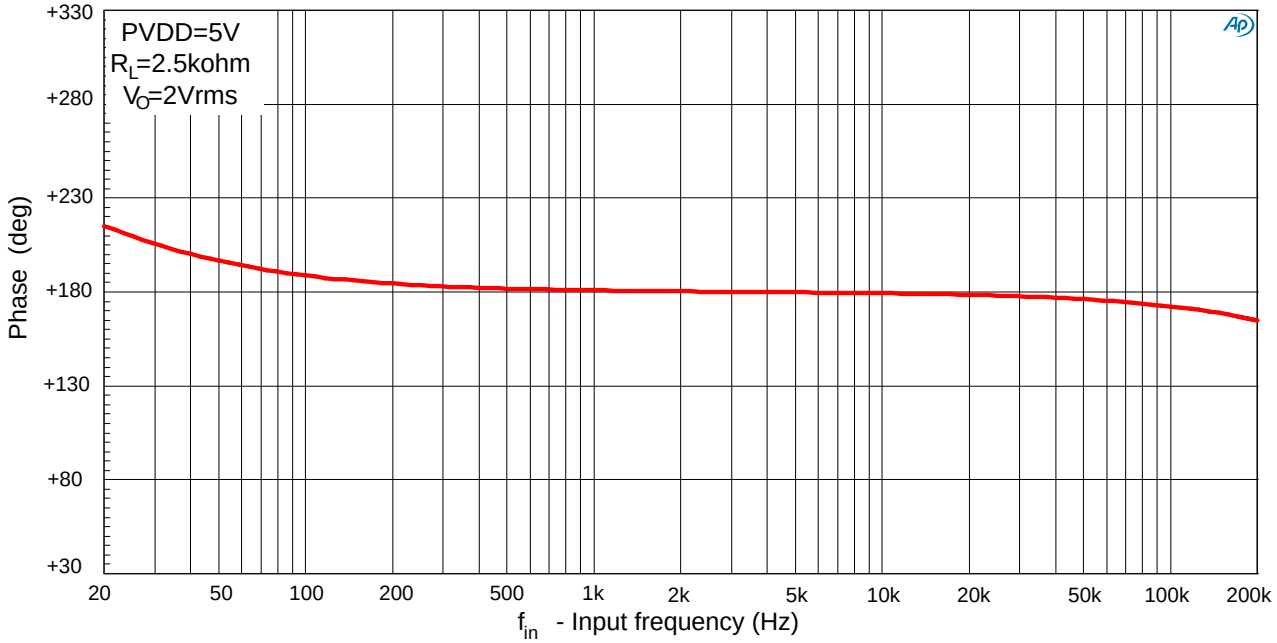
- Total Harmonic Distortion + Noise (THD+N) vs. Signal Frequency



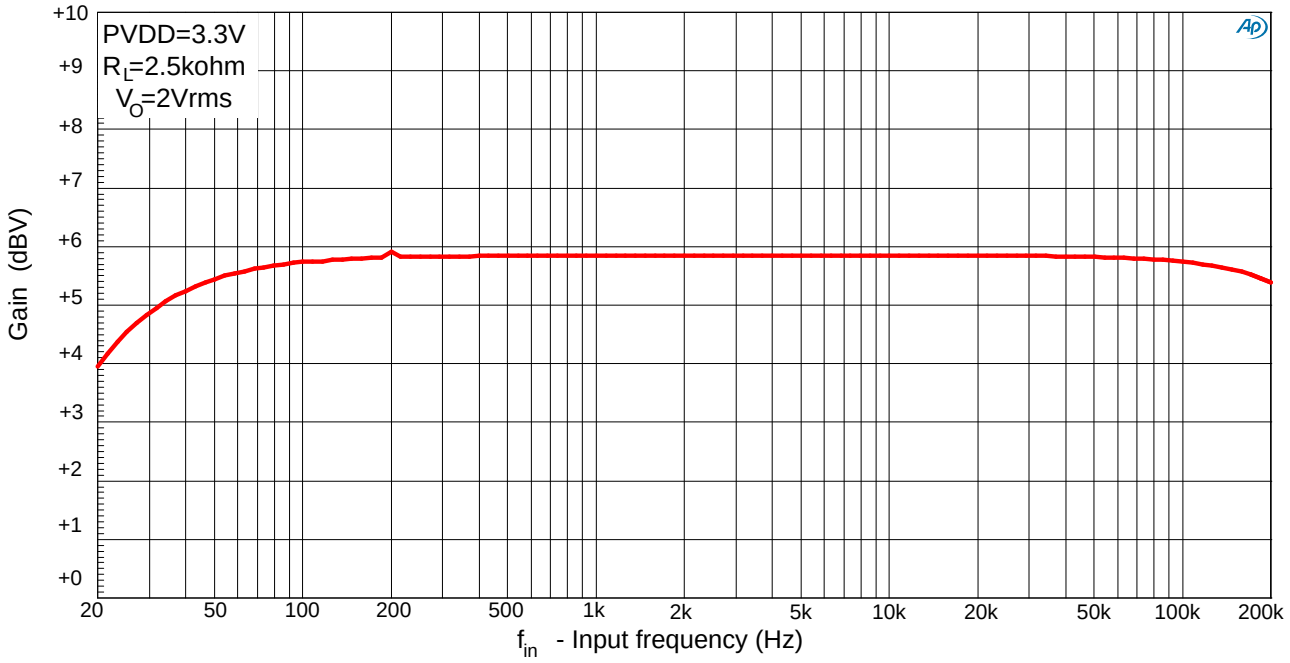


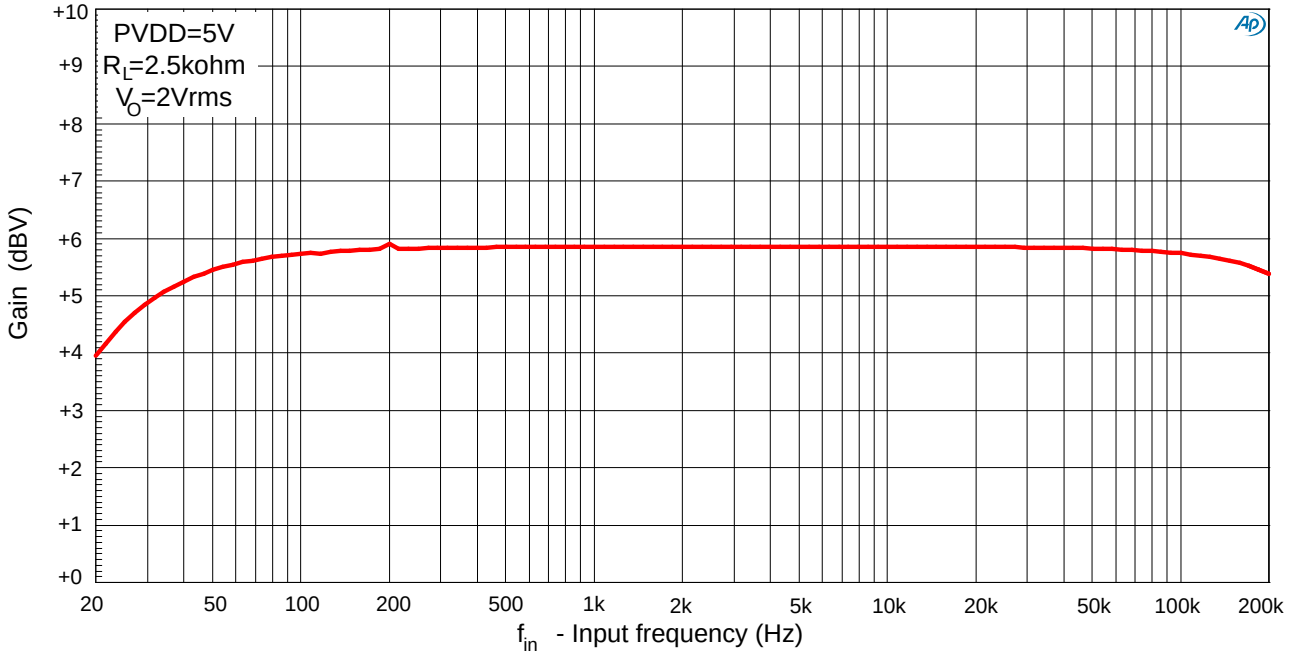
- Phase vs. Signal Frequency

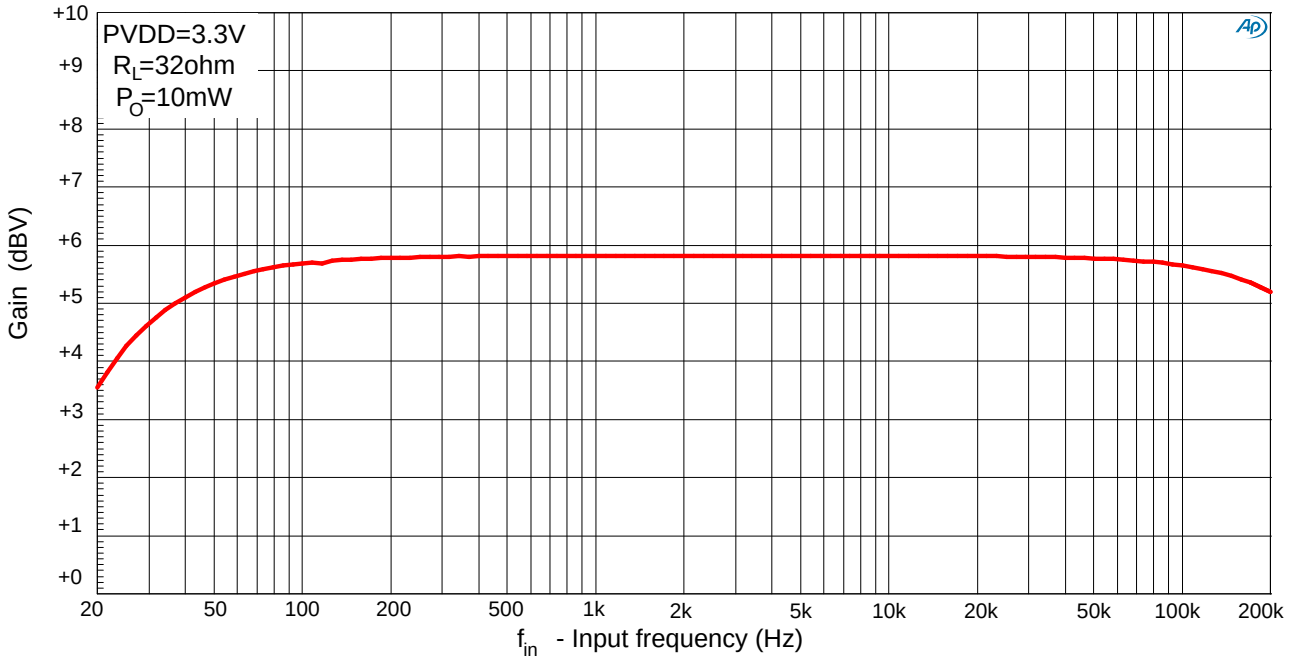


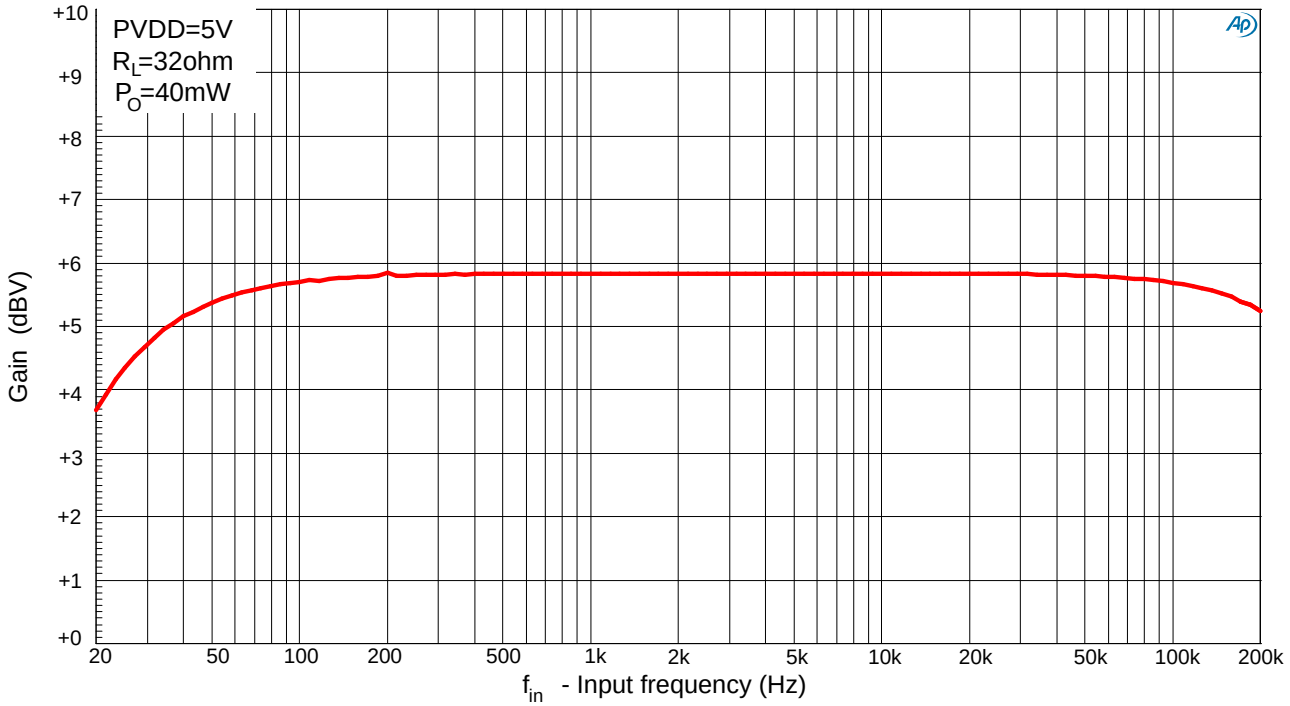


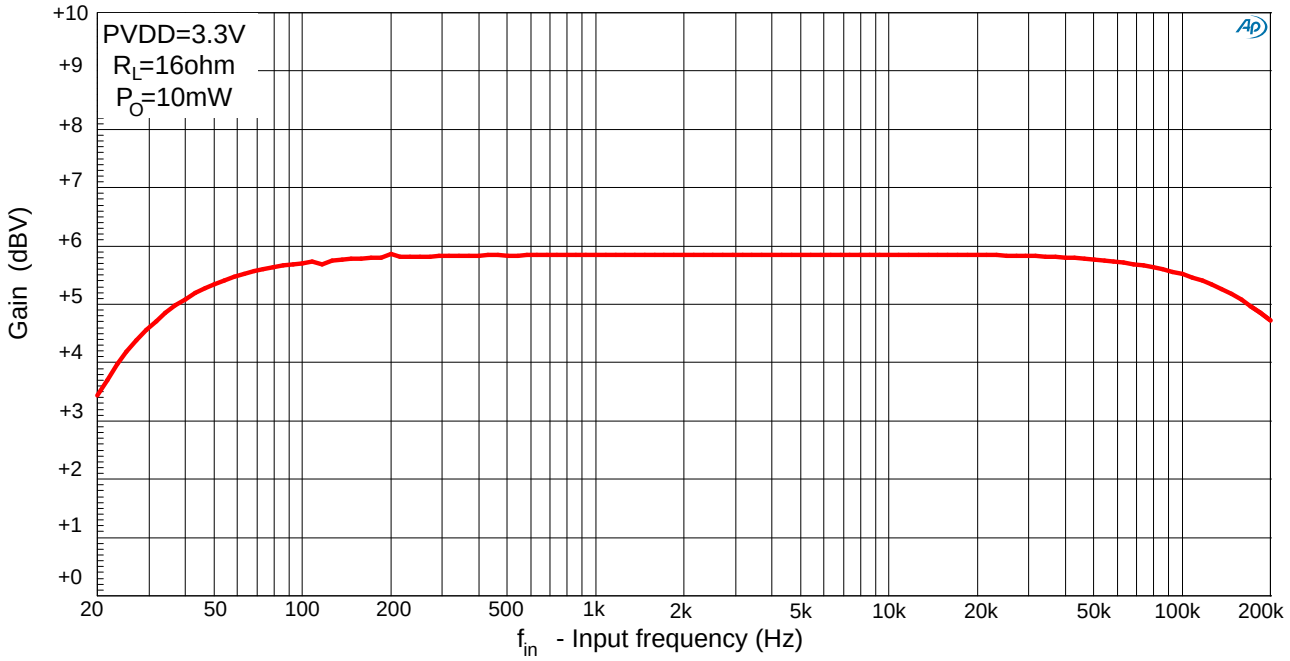
- Gain vs. Signal Frequency

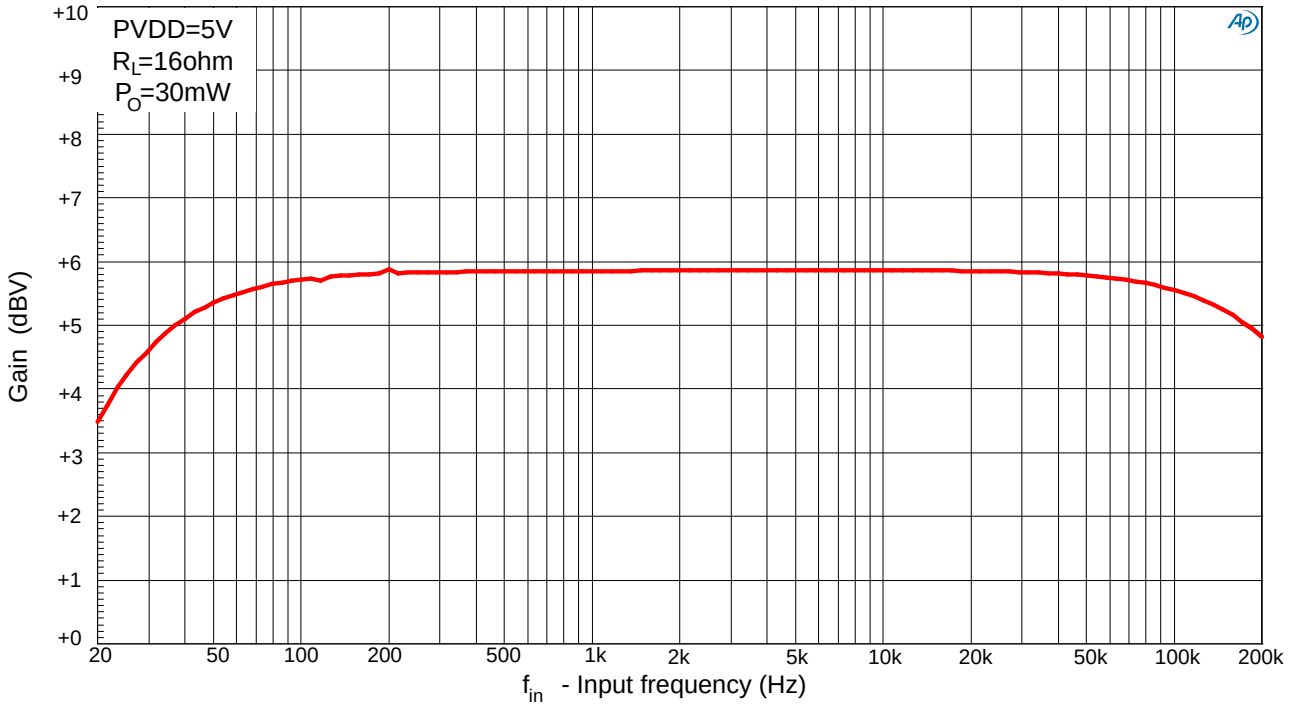





PVDD=3.3V
RL=32ohm
PO=10mW
Gain (dBV)
+10
+9
+8
+7
+6
+5
+4
+3
+2
+1
+0
20
50
100
200
500
1k
2k
5k
10k
20k
50k
100k
200k
fin - Input frequency (Hz)


PVDD=5V
RL=32ohm
PO=40mW
Gain (dBV)
+10
+9
+8
+7
+6
+5
+4
+3
+2
+1
+0
20
50
100
200
500
1k
2k
5k
10k
20k
50k
100k
200k
fin - Input frequency (Hz)


PVDD=3.3V
RL=16ohm
PO=10mW
Gain (dBV)
+10
+9
+8
+7
+6
+5
+4
+3
+2
+1
+0
20
50
100
200
500
1k
2k
5k
10k
20k
50k
100k
200k
fin - Input frequency (Hz)


PVDD=5V
RL=16ohm
PO=30mW
Gain (dBV)
+10
+9
+8
+7
+6
+5
+4
+3
+2
+1
+0
20
50
100
200
500
1k
2k
5k
10k
20k
50k
100k
200k
fin - Input frequency (Hz)

Application Information

■ Line Driver Amplifiers Operation

A conventional inverting line-driver amplifier always requires an output dc-blocking capacitor and a bypass capacitor, see Figure 1. DC blocking capacitors are large in size and cost a lot. It also restricts the output low frequency response. POP will occur if the charge and discharge processes on output capacitors are not carefully take cared. Besides, it needs to wait for a long time to charge V_{OUT} from 0V to VDD/2.

For a cap-less line driver, see figure 2, a negative supply voltage (-VDD) is produced by the integrated charge-pump, and feeds to line driver's negative supply instead of ground. The positive input can directly connect to ground without a C_{BYPASS}, and V_{OUT} is biased at ground which can eliminate the output dc-blocking capacitors. The output voltage swing is doubled compared to conventional amplifiers.

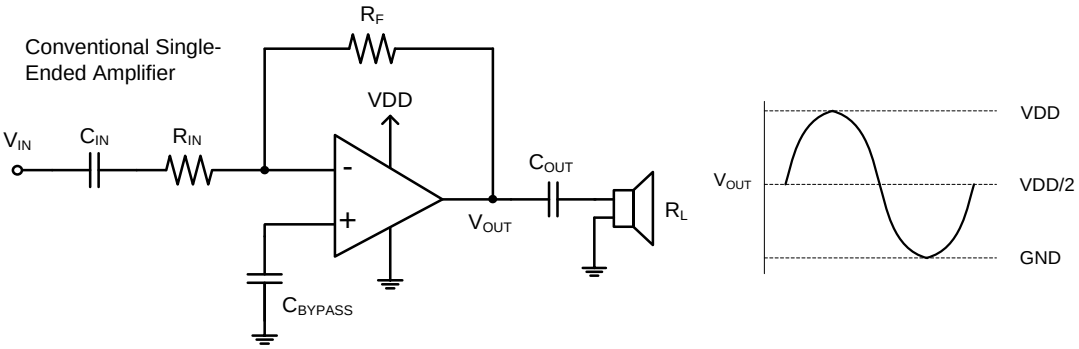


Figure 1. Conventional Line Driver Amplifier

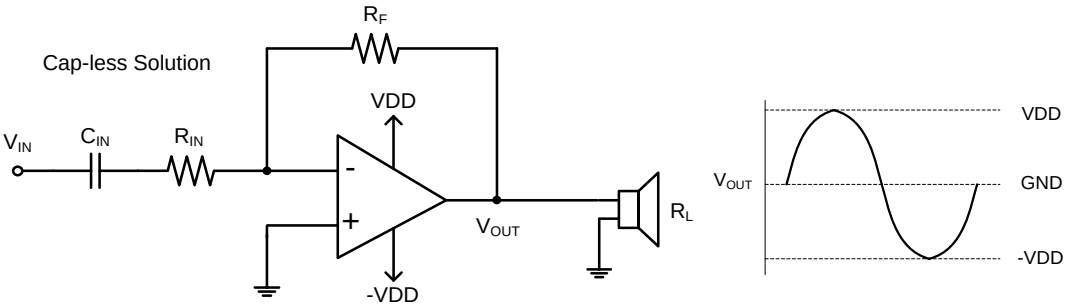


Figure 2. Cap-less Line Driver Amplifier

External Under-Voltage Protection

The external under-voltage protection is used to mute the line-driver before any input voltage change to generate a POP. The threshold of UVP pin is designed to 1.25V. By using a resistor divider, users can decide the UVP level and hysteresis level. The levels can be obtained by following equations:

$$V_{UVP} = (1.25V - 6\mu A \times R13) \times (R11 + R12) / R12$$
$$Hysteresis = 5\mu A \times R13 \times (R11 + R12) / R12$$

With the condition R13 >> (R11 // R12).

For example, to obtain V_{UVP}=2.67V, Hysteresis=0.37V, R11=1.5kΩ, R12=1kΩ, R13=30kΩ.

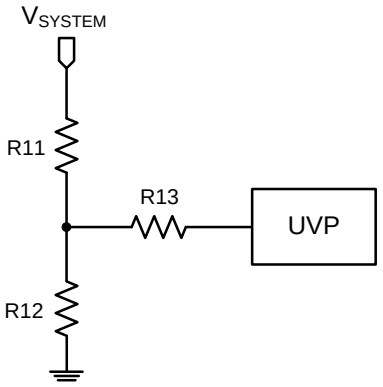
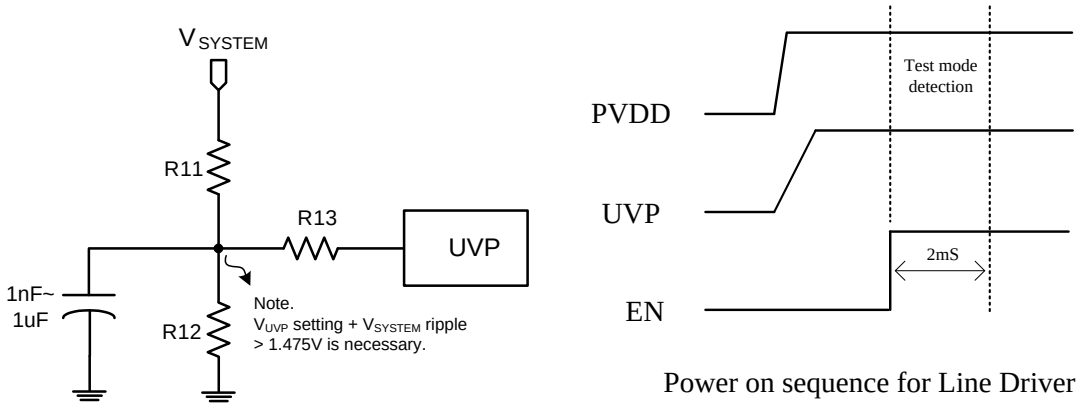


Figure 3-1. Application Circuit of UVP Pin

The UVP pin voltage ripple needs to take care during chip enable state within 2mS. The UVP pin ripple lower 1.25V~1.475V by 2~4 times will trigger test mode in Line Driver. To put a capacitor parallel with UVP pin can improve test mode mis-operating triggered while V_{STSTEM} is not stable during power up initially. V_{UVP} pin voltage threshold <1.475V shall be prohibited during chip enable state.



Power on sequence for Line Driver

UVP pin is pulled high internally, and therefore it can be floated to disable the external under-voltage protection feature.

Charge-Pump Operation

The charge-pump is used to generate a negative supply voltage to supply to line-driver. It needs two external capacitors, C_{FLY} and C_{PVSS}, for normal operation, see figure 4 (a). The operation can be analyzed with two phase. In phase I, see figure 4 (b), C_{FLY} is charged to PVDD, and in phase II, see figure 4 (c), the charges on C_{FLY} are shared with C_{PVSS}, that makes PVSS a negative voltage. After an adequate clock cycles, PVSS will be equaled to –PVDD. Low ESR capacitors are recommended, and the typical value of C_{FLY} and C_{PVSS} is 1μF. A smaller capacitance can be used, but the maximum output voltage may be reduced.

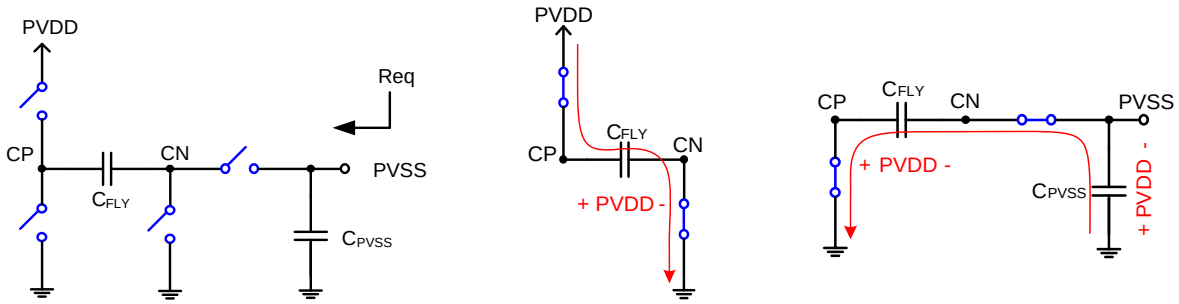


Figure 4. Charge-Pump Operation

Enable Function

The enable function is used to reduce power consumption while the device is not in use. When a logic low is applied to this pin, the overall circuits are turned off. Line driver output and PVSS are pulled to ground. When a logic high is applied to enable pin, the PVSS is started to build-up and line driver output signal is released after about 0.5ms typically.

Decoupling Capacitors

A low ESR power supply decoupling capacitor is required for better performance. The capacitor should place as close to chip as possible, the value is typically 1μF. For filtering low frequency noise signals, a 10μF or greater capacitor placed near the chip is recommended.

Input Blocking Capacitors (C_{IN})

An input blocking capacitor is required to block the dc voltage of the audio source and allows the input to bias at a proper dc level for optimum operation. The input capacitor and input resistor (R_I) form a high-pass filter with the corner frequency determined as following equation:

$$f_C = \frac{1}{2\pi R_I C_{IN}}$$

■ Gain Setting Resistors (R_I and R_F)

The line driver's gain is determined by R_I and R_F. The typical configurations of the amplifier are inverting, non-inverting, and differential input, see figure 5. The gain equations are listed as follows:

(a) Inverting configuration : $A_V = -\frac{R_F}{R_I}$

(b) Non-inverting configuration : $A_V = 1 + \frac{R_F}{R_I}$

© Differential-input configuration : $A_V = \frac{R_F}{R_I}$

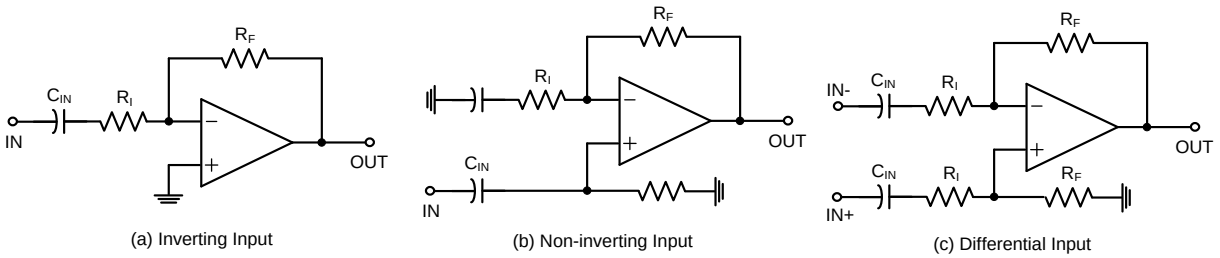


Figure 5. Line Driver Amplifier Configurations

The values of R_I and R_F must be chosen with consideration of stability, frequency response and noise. The recommended value of R_I is in the range from 1kΩ to 47kΩ, and R_F is from 4.7kΩ to 100kΩ for. The gain is in the range from -1V/V to -10V/V for inverting configuration. Table 1 lists the recommended resistor values for different configurations.

R_I (kΩ)	R_F (kΩ)	Inverting Input Gain (V/V)	Non-inverting Input Gain (V/V)	Differential Input Gain (V/V)
22	22	-1	2	1
15	30	-2	3	2
33	68	-2.1	3.1	2.1
10	100	-10	11	10

Table 1. Recommended Resistor Values

■ Second-Order Filter Configuration

AD22650 can be used like a standard OPAMP. Several filter topologies can be implemented by using AD22650, both single-ended and differential input configuration, see figure 6. For inverting input configuration, the overall gain is $-\frac{R2}{R1}$, the high-pass filter's cutoff frequency is $\frac{1}{2\pi R1C3}$, the low-pass filter's cutoff frequency is $\frac{1}{2\pi\sqrt{R2R3C1C2}}$, The detail component values are listed on table 2.

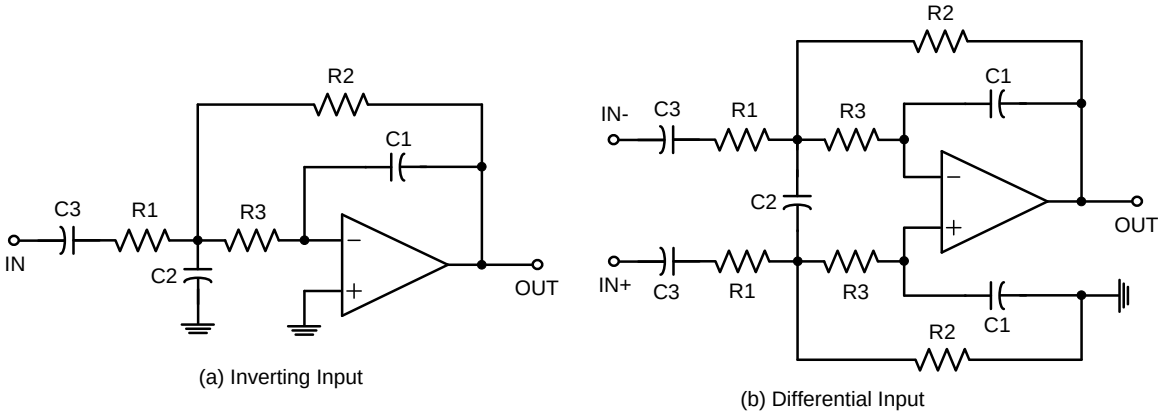


Figure 6. Second-order Active Low-Pass Filter

Gain (V/V)	High Pass (Hz)	Low Pass (kHz)	C1 (pF)	C2 (pF)	C3 (μF)	R1 (kΩ)	R2 (kΩ)	R3 (kΩ)
-1	1.6	40	100	680	10	10	10	24
-1.5	1.3	40	68	680	15	8.2	12	30
-2	1.6	60	33	150	6.8	15	30	47
-2	1.6	30	47	470	6.8	15	30	43
-3.33	1.2	30	33	470	10	13	43	43
-10	1.5	30	22	1000	22	4.7	47	27

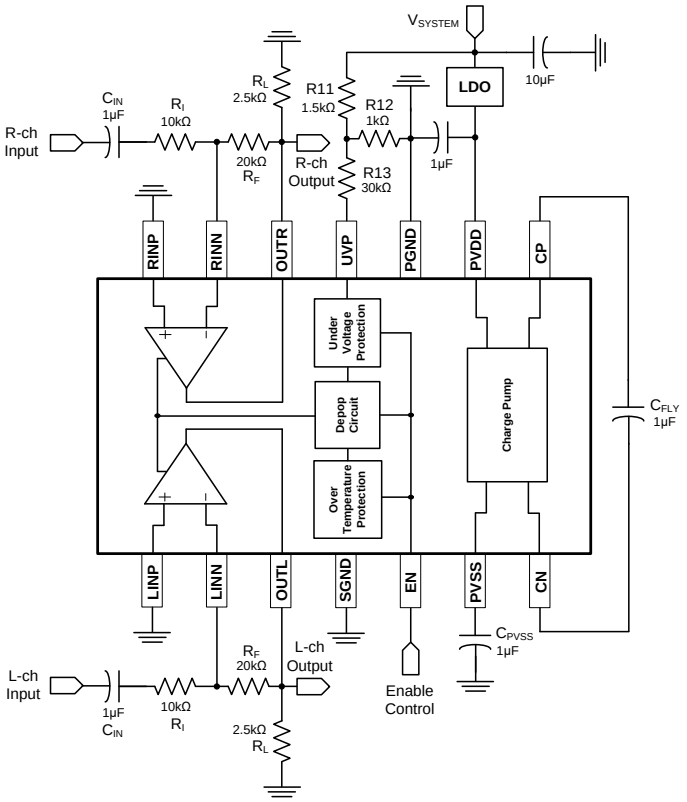
Table 2. Second-order Low-Pass Filter Specifications

■ Over-Temperature Protection

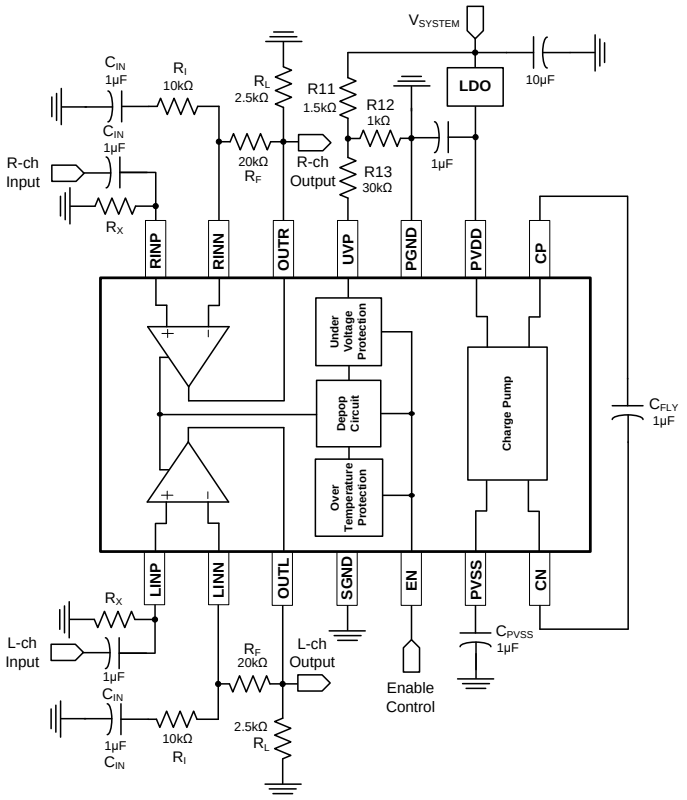
AD22650 provide an over-temperature protection to limit the junction temperature to 150℃. As junction temperature exceeds 150℃, internal thermal sensor will turn off the drivers immediately. The drivers will turn on again if the junction temperature is smaller than 130℃. A 20℃ hysteresis is designed to lower the average junction temperature during continuous thermal overload conditions, increasing lifetime of the chip.

Typical Application Circuit

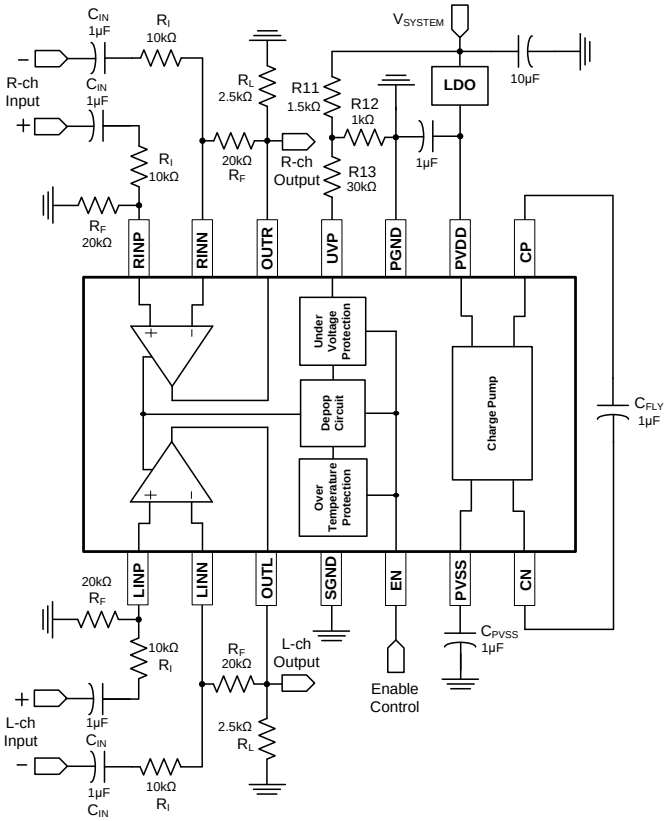
■ Inverting Input Line Driver Amplifier



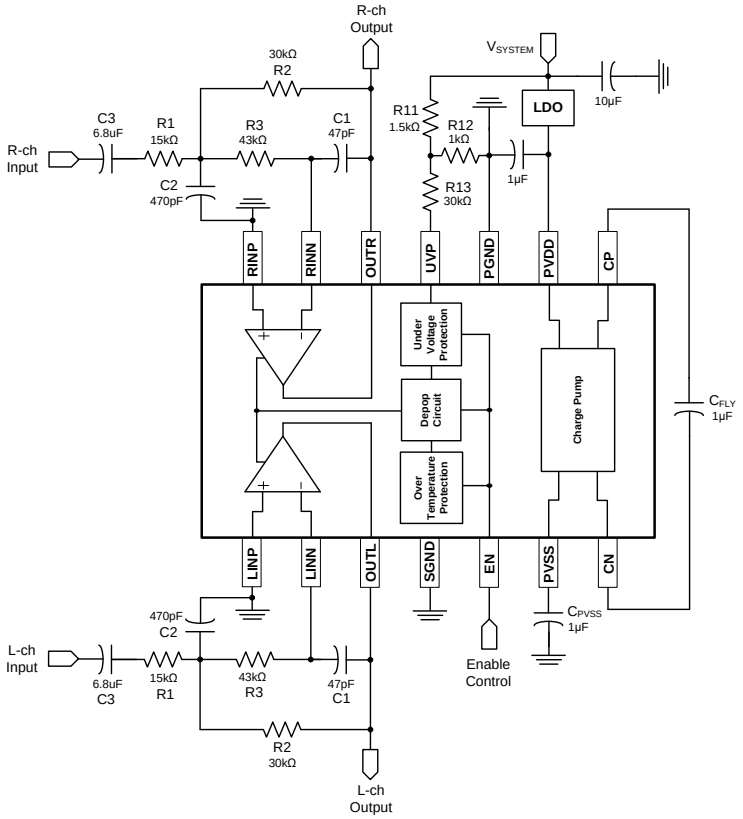
■ Non-inverting Input Line Driver Amplifier



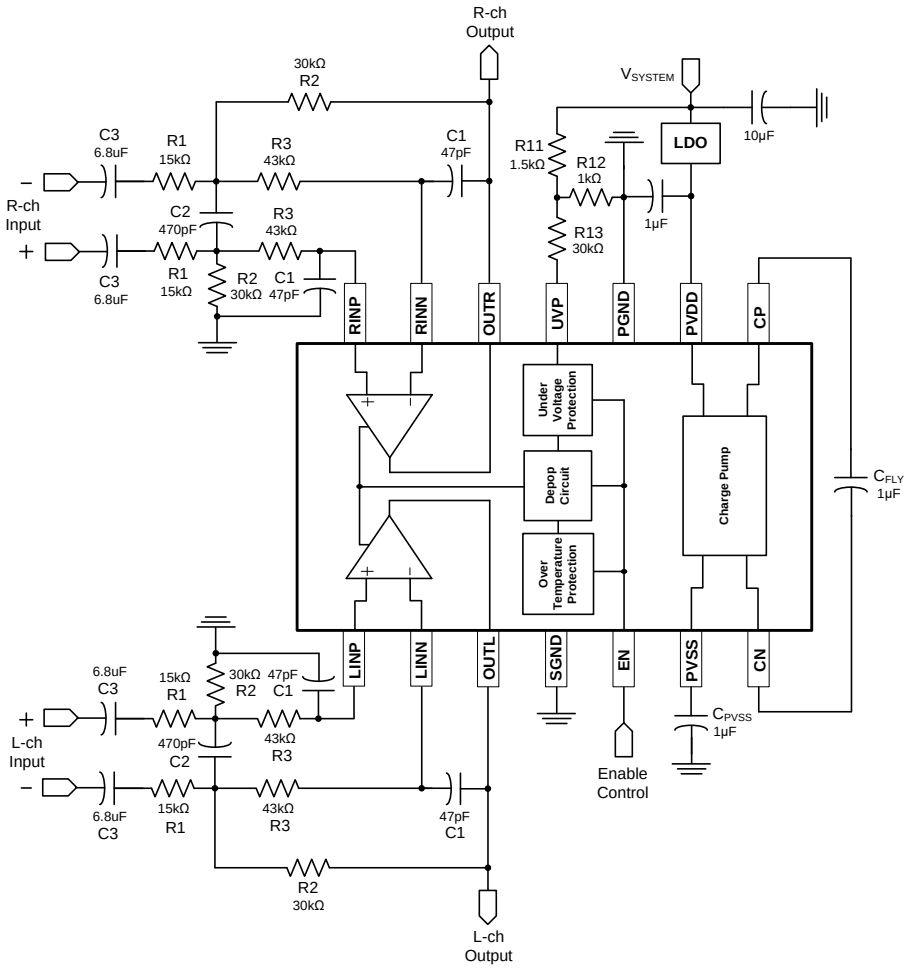
■ Differential Input Line Driver Amplifier



■ Inverting Input Second-Order Active Low-Pass Filter (load support >= 600Ω only)

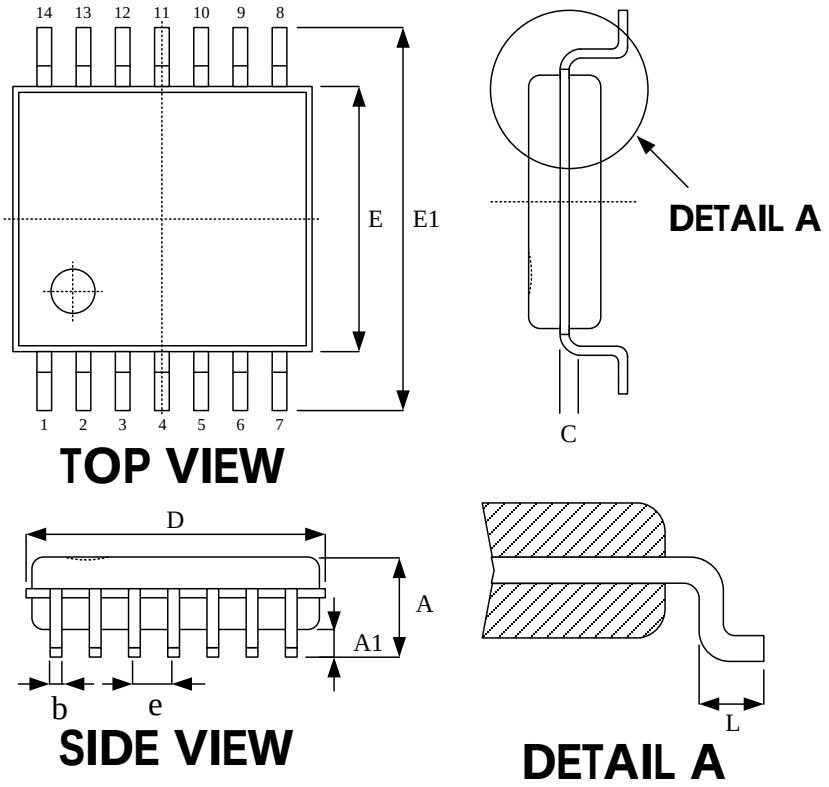


■ Differential Input Second-Order Active Low-Pass Filter (load support >= 600Ω only)



Package Outline Drawing

TSSOP-14L



Symbol	Dimension in mm	
	Min	Max
A	--	1.20
A1	0.05	0.15
b	0.19	0.30
c	0.09	0.16
D	4.90	5.10
E	4.30	4.50
E1	6.30	6.50
e	0.65 BSC	
L	0.45	0.75

Revision History

Revision	Date	Description
0.1	2011.11.02	Initial version
0.2	2011.12.15	Modify the ordering information
0.3	2012.03.29	Modify the description of T_J in Absolute Maximum Ratings Remove the description of TJ in Recommended Operating Conditions
1.0	2012.09.14	Remove “Preliminary”
1.1	2012.12.14	Modify the Pin Description
1.2	2013.05.06	Modify the Pin Description and the External Under Voltage Protection
1.3	2013.06.17	Modify the minimum VIH and maximum VIL of EN
1.4	2013.07.18	Modify ISD max spec from 100uA to 5uA with V_{DD} =5.5V
1.5	2014.02.11	Modify TA from 0~70’C to -40~85’C
1.6	2015.03.11	Change minimum load from 600ohm to 16ohm Add 16 and 32ohm data into Electrical Characteristics and Typical Characteristics Modify Package Outline Drawing
1.7	2016.02.15	Added UVP description into datasheet.
1.8	2018.01.04	Update typical application circuit
1.9	2018.09.07	Update UVP description.

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